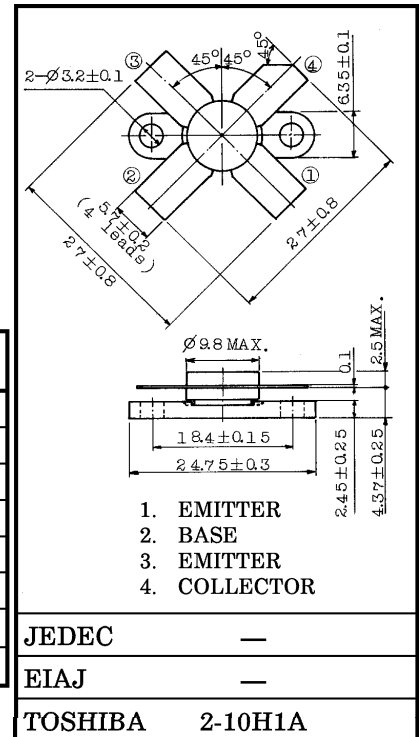


(LOW SUPPLY VOLTAGE USE)

- Specified 12.5V, 28MHz Characteristics
- Output Power : $P_o = 20W_{PEP}$ (Min.)
- Power Gain : $G_p = 12dB$ (Min.)
- Collector Efficiency : $\eta_C = 35%$ (Min.)
- Intermodulation Distortion : $IMD = -30dB$ (Max.)

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CES}	40	V
Collector-Emitter Voltage	V_{CEO}	18	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	6	A
Collector Power Dissipation	P_C	60	W
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_{stg}	-65~175	°C


ELECTRICAL CHARACTERISTICS (Tc = 25°C)

Weight : 4.0g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50mA, I_B = 0$	18	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = 50mA, V_{EB} = 0$	40	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1mA, I_C = 0$	4	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 5A$ *	20	—	185	
Transition Frequency	f_T	$V_{CE} = 5V, I_C = 0.5A$	—	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 12.5V, I_E = 0$ $f = 1MHz$	—	—	250	pF
Power Gain	G_p	$V_{CC} = 12.5V, f_1 = 28.000$ MHz, $f_2 = 28.001MHz$	12.0	—	—	dB
Input Power	P_i		—	—	1.2	W_{PEP}
Collector Efficiency	η_C	$I_{idle} = 25mA$	35	45	—	%
Intermodulation Distortion	IMD	$P_o = 20W_{PEP}$ (Fig.)	—	—	-30	dB
Series Equivalent Input Impedance	Z_{in}	$V_{CC} = 12.5V, f_1 = 28.000$ MHz, $f_2 = 28.001MHz$	—	1.1 -j0.25	—	Ω
Series Equivalent Output Impedance	Z_{out}	$P_o = 20W_{PEP}$	—	3.0 -j0.75	—	Ω

Note : Above parameters , ratings , limits and conditions are subject to change.